N-Channel 200-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

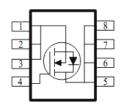
Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)	
200	400 @ V _{GS} = 10V	3	
	450 @ V _{GS} = 4.5V	2.8	







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			200	V			
Gate-Source Voltage		V_{GS}	±20	V			
Continuous Drain Current a	T _A =25°C		3	А			
Continuous Drain Current	T _A =70°C	l _D	2.4				
Pulsed Drain Current ^b		I _{DM}	20				
Continuous Source Current (Diode Conduction) a		I_S	6.2	Α			
Power Dissipation ^a	T _A =25°C	P_{D}	5	W			
Power Dissipation	T _A =70°C	' D	3.2	V V			
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State		65	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

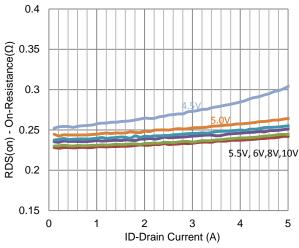
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, ID = 250 uA	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	uA	
Zero Gate Voltage Drain Current		$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}$	1		uA		
Zero Gate Voltage Brain Gunerit	I _{DSS}	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 3.0 \text{ A}$			400	mΩ	
Dialii-Source On-Nesistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 2.8 \text{ A}$			450	11122	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 3.0 \text{ A}$		10		S	
Diode Forward Voltage	V_{SD}	$I_S = 3.1 \text{ A}, V_{GS} = 0 \text{ V}$		0.77		V	
		Dynamic					
Total Gate Charge	Q_g			7.9			
Gate-Source Charge	Q_{gs}	$V_{DS} = 100 \text{ V}, V_{GS} = 4.5 \text{ V}, ID = 2.0 \text{ A}$		3.4		nC	
Gate-Drain Charge	Q_{gd}			3.9			
Turn-On Delay Time	t _{d(on)}			3.7			
Rise Time	t _r	$V_{DD} = 100 \text{ V}, R_L = 50 \Omega, I_D = 2.0 \text{ A},$		8		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		26		ns	
Fall Time	t _f			12			
Input Capacitance	C _{iss}			807			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		81		pF	
Reverse Transfer Capacitance	C_{rss}			38			

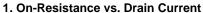
Notes

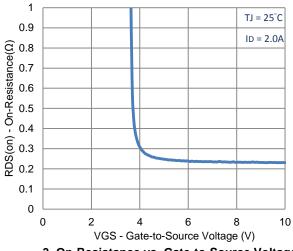
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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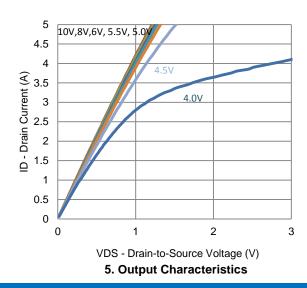
Typical Electrical Characteristics





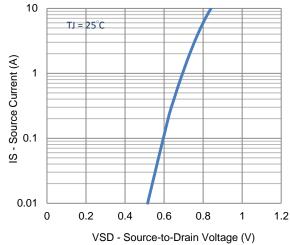


3. On-Resistance vs. Gate-to-Source Voltage

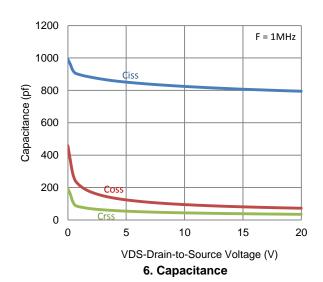


10 $TJ = 25^{\circ}C$ 9 8 ID - Drain Current (A) 6 5 4 3 2 1 0 2 6 VGS - Gate-to-Source Voltage (V)

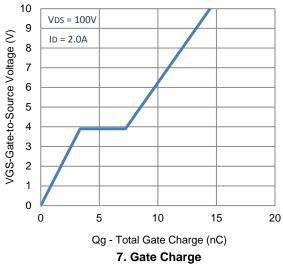
2. Transfer Characteristics



4. Drain-to-Source Forward Voltage

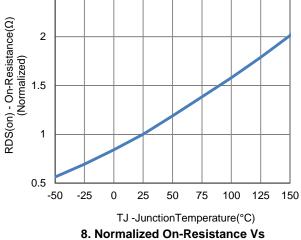


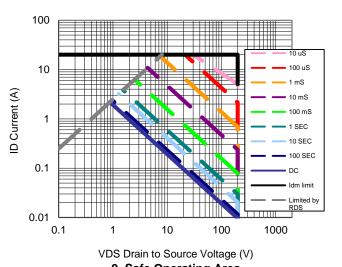
Typical Electrical Characteristics



8. Normalized On-Resistance
Junction Temperature

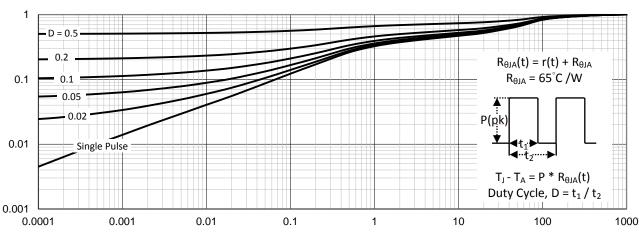
2.5





160 PEAK TRANSIENT POWER (W) 140 120 100 80 60 40 20 0 0.01 1000 0.001 0.1 10 100 t1 TIME (SEC) 10. Single Pulse Maximum Power Dissipation

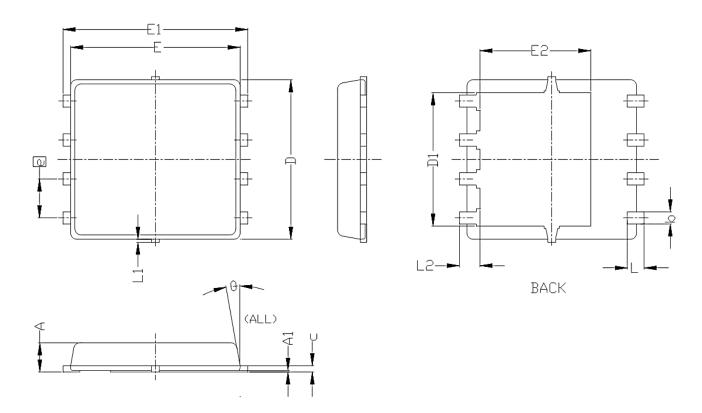




t1 TIME (sec)

11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0. 039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0. 15	0. 20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC				0. 205 BSC		
D1	4. 35 BSC				0. 171 BSC		
E	5, 55 BSC			0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC				0. 143 BSC		
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0. 15	0		0.006	
L2	0.68 REF			0. 027 REF			
θ	0°		10°	0°		10°	